

TrenchMV™ Power MOSFET

IXTF200N10T

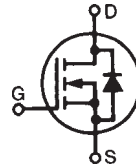
$$V_{DSS} = 100V$$

$$I_{D25} = 90A$$

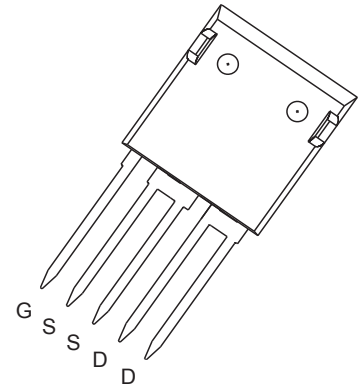
$$R_{DS(on)} \leq 7m\Omega$$

(Electrically Isolated Back Surface)

N-Channel Enhancement Mode
Avalanche Rated



ISOPLUS i4-Pak™ (5-lead)



G = Gate D = Drain
S = Source

Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ\text{C}$ to 175°C	100	V
V_{DGR}	$T_J = 25^\circ\text{C}$ to 175°C , $R_{GS} = 1M\Omega$	100	V
V_{GSM}	Transient	± 30	V
I_{D25}	$T_C = 25^\circ\text{C}$	90	A
I_{DM}	$T_C = 25^\circ\text{C}$, Pulse Width Limited by T_{JM}	500	A
I_A	$T_C = 25^\circ\text{C}$	40	A
E_{AS}	$T_C = 25^\circ\text{C}$	1.5	J
P_D	$T_C = 25^\circ\text{C}$	156	W
T_J		-55 ... +175	$^\circ\text{C}$
T_{JM}		175	$^\circ\text{C}$
T_{stg}		-55 ... +175	$^\circ\text{C}$
T_L	1.6mm (0.062in.) from Case for 10s Plastic Body for 10 seconds	300 260	$^\circ\text{C}$ $^\circ\text{C}$
V_{ISOL}	50/60Hz, $t = 1$ minute, $I_{ISOL} < 1\text{mA}$, RMS	2500	V
M_d	Mounting Force	120..120 / 4.5..27	N/lb.
Weight		6	g

Features

- Silicon Chip on Direct-Copper Bond (DCB) Substrate
- Isolated Mounting Surface
- Avalanche Rated
- 2500V Electrical Isolation

Advantages

- Easy to Mount
- Space Savings
- High Power Density

Applications

- Automotive
 - Motor Drives
 - High Side Switch
 - 12V Battery
 - ABS Systems
- DC/DC Converters and Off-Line UPS
- Primary - Side Switch
- High Current Switching Applications

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$ Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{DSS}	$V_{GS} = 0V$, $I_D = 250\mu\text{A}$	100		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250\mu\text{A}$	2.5		4.5 V
I_{GSS}	$V_{GS} = \pm 20V$, $V_{DS} = 0V$			± 200 nA
I_{DSS}	$V_{DS} = V_{DSS}$, $V_{GS} = 0V$ $T_J = 150^\circ\text{C}$			5 μA 250 μA
$R_{DS(on)}$	$V_{GS} = 10V$, $I_D = 50A$, Notes 1			7 m Ω

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
g_{fs}	$V_{DS} = 10\text{V}$, $I_D = 60\text{A}$, Note 1	60	96	S
C_{iss}	$V_{GS} = 0\text{V}$, $V_{DS} = 25\text{V}$, $f = 1\text{MHz}$		9400	pF
C_{oss}			1087	pF
C_{rss}			140	pF
$t_{d(on)}$	Resistive Switching Times $V_{GS} = 10\text{V}$, $V_{DS} = 0.5 \cdot V_{DSS}$, $I_D = 50\text{A}$ $R_G = 3.3\Omega$ (External)		35	ns
t_r			31	ns
$t_{d(off)}$			45	ns
t_f			34	ns
$Q_{g(on)}$	$V_{GS} = 10\text{V}$, $V_{DS} = 0.5 \cdot V_{DSS}$, $I_D = 50\text{A}$		152	nC
Q_{gs}			47	nC
Q_{gd}			47	nC
R_{thJC}				0.96 $^\circ\text{C/W}$
R_{thCH}		0.21		$^\circ\text{C/W}$

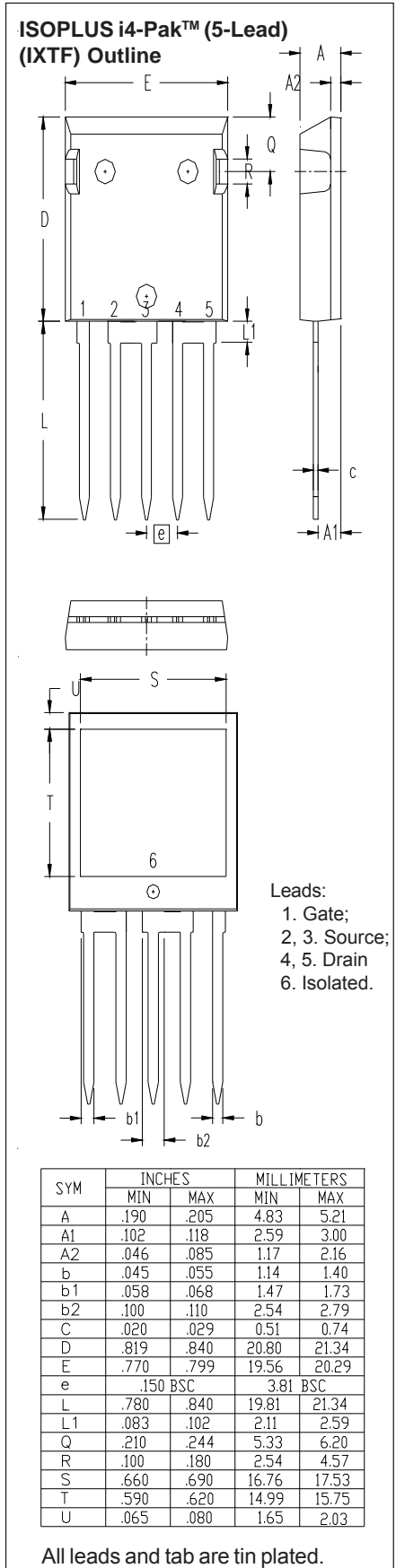
Source-Drain Diode

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
I_S	$V_{GS} = 0\text{V}$			200 A
I_{SM}	Repetitive, Pulse Width Limited by T_{JM}			500 A
V_{SD}	$I_F = 50\text{A}$, $V_{GS} = 0\text{V}$, Note 1			1.0 V
t_{rr}	$I_F = 100\text{A}$, $V_{GS} = 0\text{V}$, $-di/dt = 100\text{A}/\mu\text{s}$ $V_R = 50\text{V}$		76	ns
Q_{RM}			205	nC
I_{RM}			5.4	A

Notes: 1. Pulse Test, $t \leq 300\mu\text{s}$; Duty Cycle, $d \leq 2\%$.

PRELIMINARY TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from data gathered during objective characterizations of preliminary engineering lots; but also may yet contain some information supplied during a pre-production design evaluation. IXYS reserves the right to change limits, test conditions, and dimensions without notice.



IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered 4,835,592 4,931,844 5,049,961 5,237,481 6,162,665 6,404,065 B1 6,683,344 6,727,585 7,005,734 B2 7,157,338B2
by one or more of the following U.S. patents: 4,850,072 5,017,508 5,063,307 5,381,025 6,259,123 B1 6,534,343 6,710,405 B2 6,759,692 7,063,975 B2
4,881,106 5,034,796 5,187,117 5,486,715 6,306,728 B1 6,583,505 6,710,463 6,771,478 B2 7,071,537

Fig. 1. Output Characteristics @ 25°C

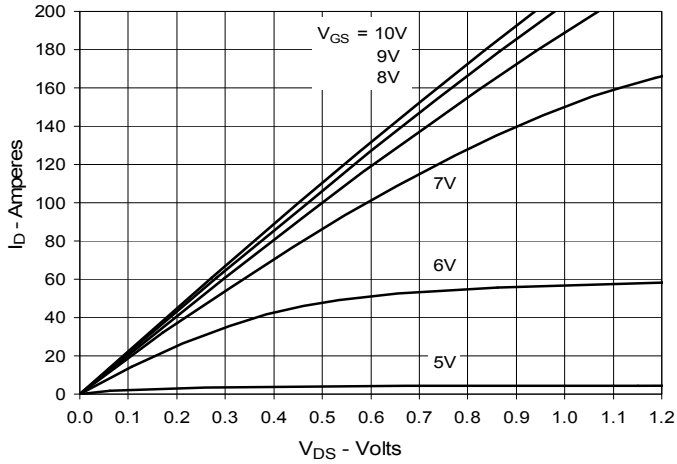


Fig. 2. Extended Output Characteristics @ 25°C

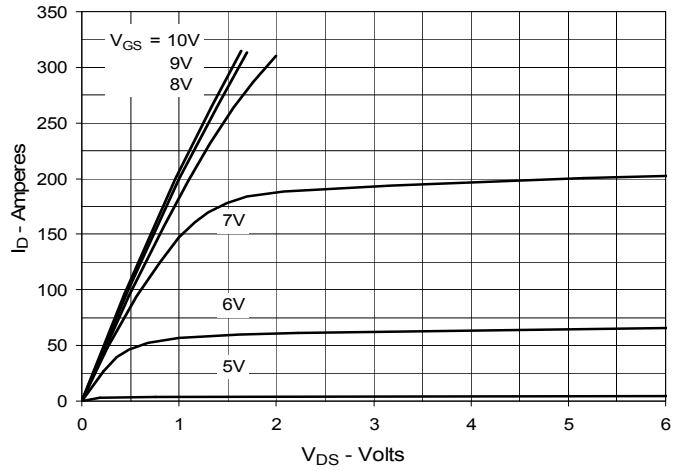


Fig. 3. Output Characteristics @ 150°C

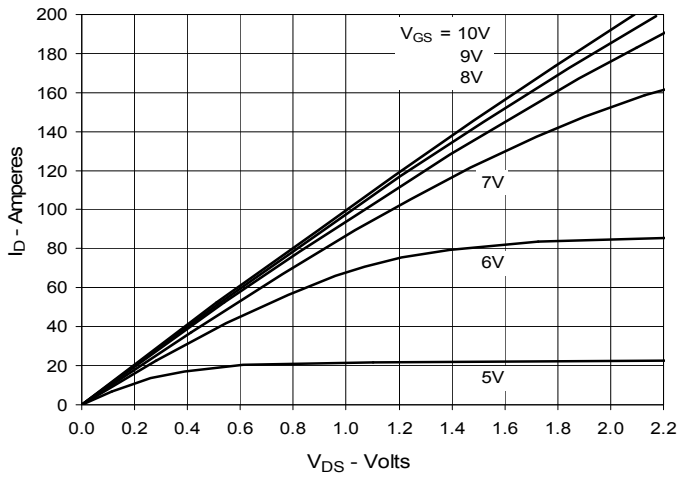


Fig. 4. $R_{DS(on)}$ Normalized to $I_D = 100A$ Value vs. Junction Temperature

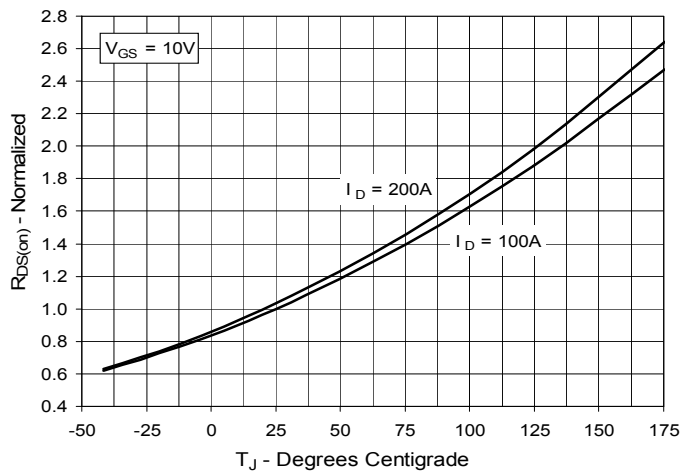


Fig. 5. $R_{DS(on)}$ Normalized to $I_D = 100A$ Value vs. Drain Current

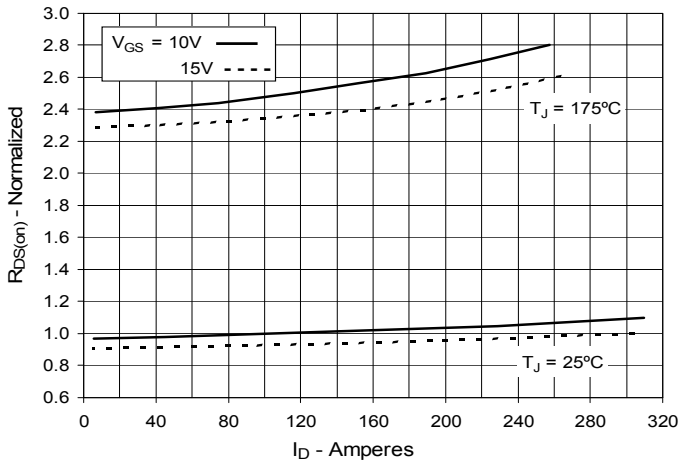


Fig. 6. Drain Current vs. Case Temperature

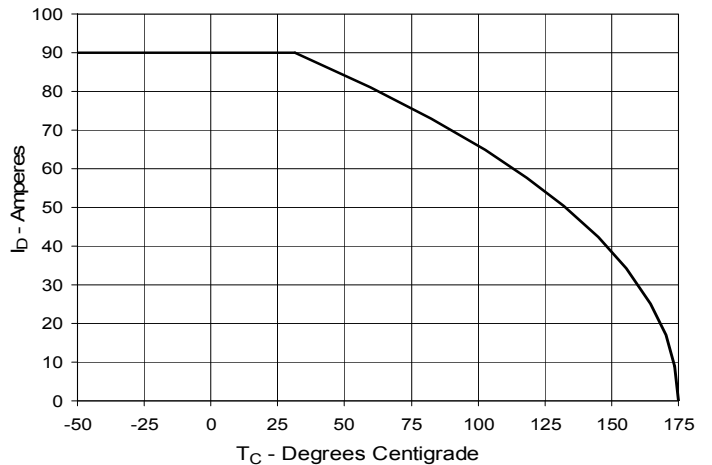


Fig. 7. Input Admittance

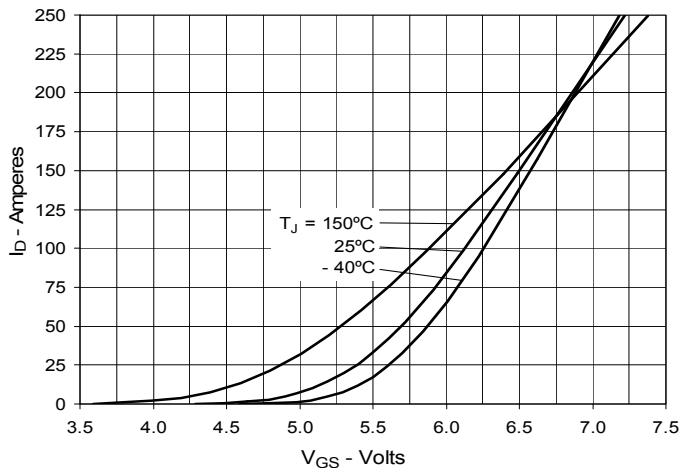


Fig. 8. Transconductance

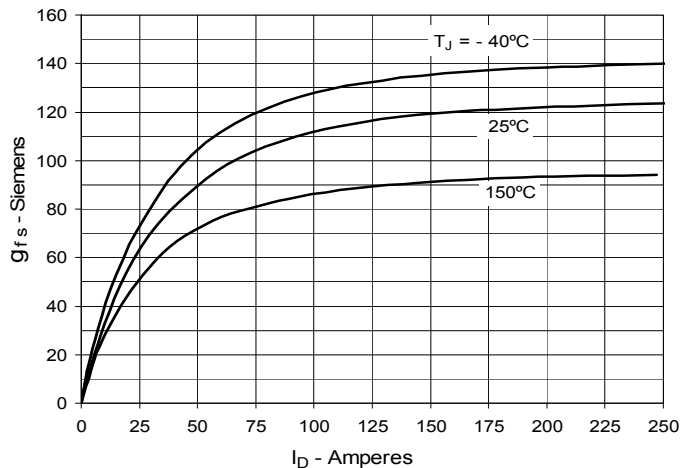


Fig. 9. Forward Voltage Drop of Intrinsic Diode

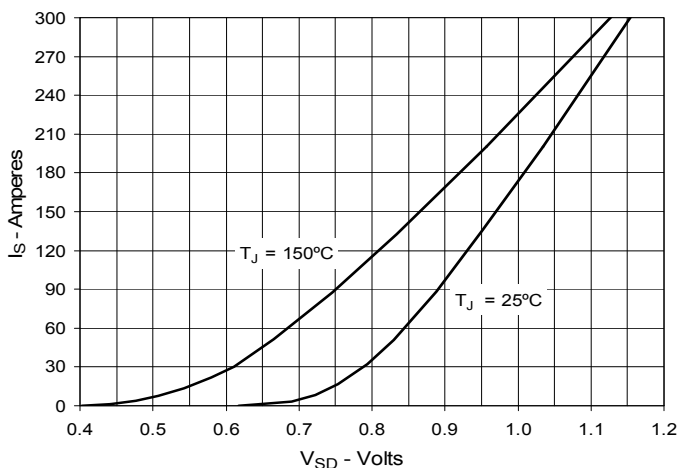


Fig. 10. Gate Charge

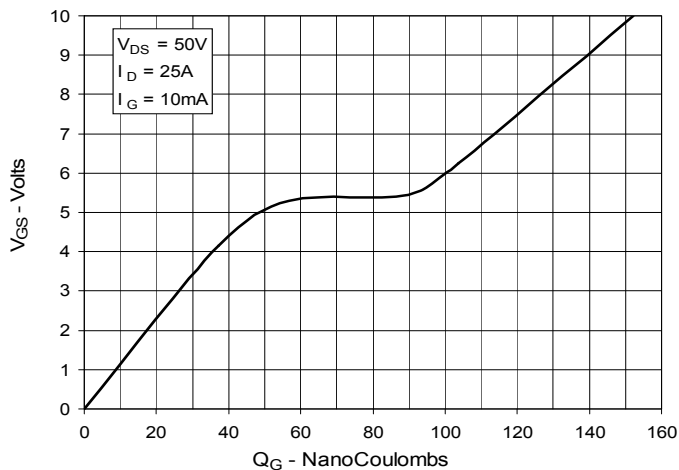


Fig. 11. Capacitance

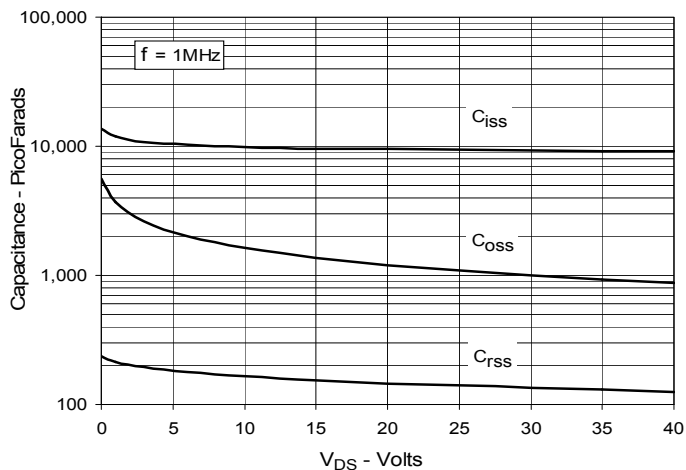


Fig. 12. Maximum Transient Thermal Impedance

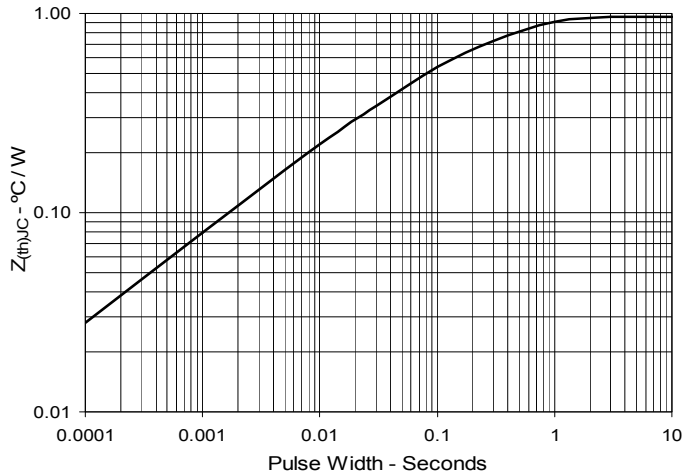


Fig. 13. Resistive Turn-on Rise Time vs. Junction Temperature

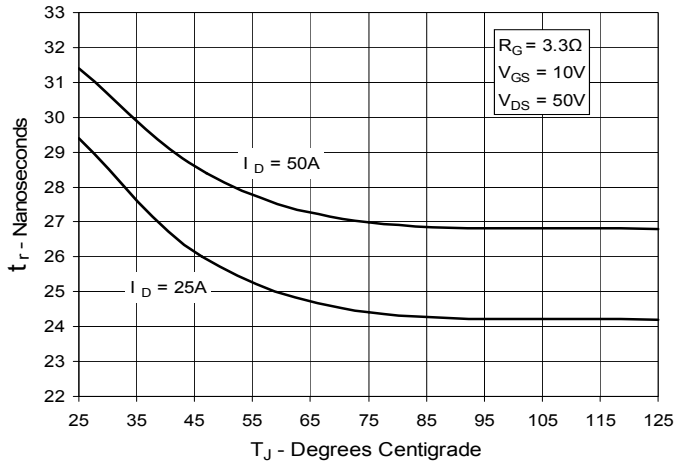


Fig. 14. Resistive Turn-on Rise Time vs. Drain Current

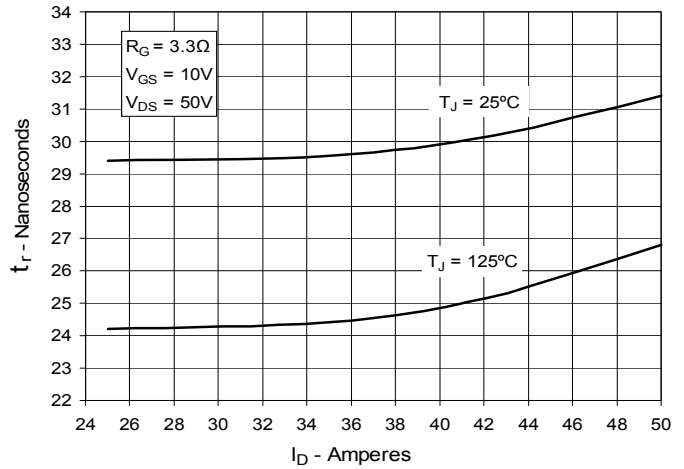


Fig. 15. Resistive Turn-on Switching Times vs. Gate Resistance

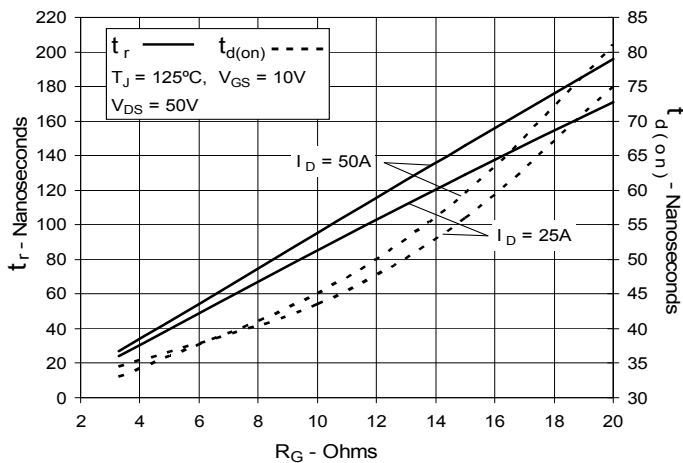


Fig. 16. Resistive Turn-off Switching Times vs. Junction Temperature

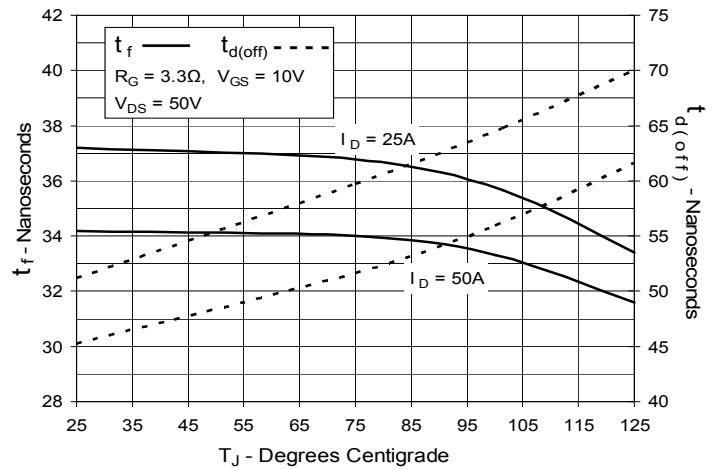


Fig. 17. Resistive Turn-off Switching Times vs. Drain Current

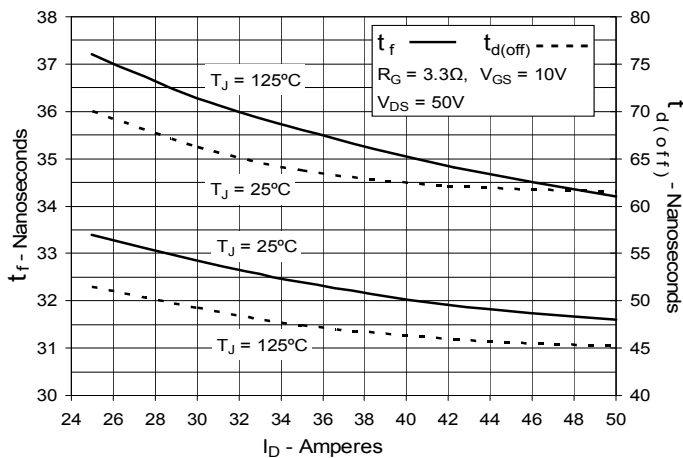


Fig. 18. Resistive Turn-off Switching Times vs. Gate Resistance

